

## CLAIMS

What is claimed is:

- 0902334-0139B
- 1 1. A memory module comprising:  
2 a plurality of memory devices; and  
3 a memory module controller configured to receive a memory  
4 transaction from a first memory bus and to control access to the plurality of  
5 memory devices.
- 1 2. The memory module of claim 1, wherein the memory module  
2 controller receives the memory transaction in a first format and reformats the  
3 memory transaction into a second format, the memory module controller  
4 providing the reformatted memory transaction to at least one of the plurality  
5 of memory devices.
- 1 3. The memory module of claim 1, further comprising a second memory  
2 bus coupled between the memory module controller and the plurality of  
3 memory devices.
- 1 4. The memory module of claim 3, wherein the second memory bus  
2 comprises separate address, data, and control signal lines.
- 1 5. The memory module of claim 1, wherein the second memory bus  
2 comprises a clock signal.
- 1 6. The memory module of claim 1, wherein the first memory bus  
2 operates at a first data rate and the second memory bus operates at a second  
3 data rate, wherein the first data rate is different than the second data rate.

1 7. The memory module of claim 1, wherein the first memory bus has a  
2 first number of signals lines and the second memory bus has a second  
3 number of signal lines, wherein the first number of signal lines is different  
4 than the second number of signal lines.

1 8. The memory module of claim 1, wherein the memory module  
2 controller comprises:  
3 request handling circuitry structured to receive the memory  
4 transaction from the first memory bus; and  
5 control logic coupled to the request handling circuitry and reformatting  
6 the memory transaction, the memory module controller providing the  
7 reformatted memory transaction to at least one of the plurality of memory  
8 devices.

1 9. The memory module of claim 1, wherein the first memory bus carries  
2 time-multiplexed data and address information, and the second memory bus  
3 includes separate address and data lines.

1 10. The memory module of claim 1, wherein the memory module is a  
2 dual in-line first memory module (DIMM).

1 11. The memory module of claim 1, wherein the memory module is a  
2 single in-line first memory module (SIMM).

1 12. The memory module of claim 1, wherein the plurality of memory  
2 devices comprise volatile memory devices.

1 13. The memory module of claim 1, wherein the plurality of memory  
2 devices comprise nonvolatile memory devices.

